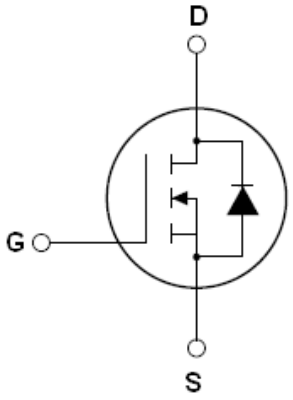
N-Channel Super Junction Power MOSFET Ⅲ

General Description

The series of devices use advanced trench gate super junction technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

V_{DS}	800	V
$R_{DS(ON)\ MAX}$	420	mΩ
I_D	11	A



Schematic diagram

Features

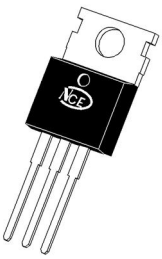
- New technology for high voltage device
- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested
- ROHS compliant

Application

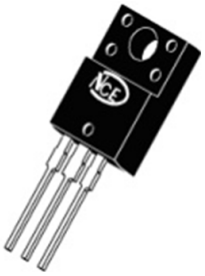
- Power factor correction（PFC）
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply（UPS）

Package Marking And Ordering Information

Device	Device Package	Marking
NCE80T420	TO-220	NCE80T420
NCE80T420F	TO-220F	NCE80T420F



TO-220



TO-220F

Table 1. Absolute Maximum Ratings (T_C=25℃)

Parameter	Symbol	NCE80T420	NCE80T420F	Unit
Drain-Source Voltage (V_{GS}=0V)	V_{DS}	800		V
Gate-Source Voltage (V_{DS}=0V), AC (f>1 Hz)	V_{GS}	±30		V
Continuous Drain Current at T_C=25°C	$I_{D\ (DC)}$	11	11*	A
Continuous Drain Current at T_C=100°C	$I_{D\ (DC)}$	8.5	8.5*	A
Pulsed drain current **(Note 1)**	$I_{DM\ (pluse)}$	44	44*	A
Maximum Power Dissipation(T_C=25℃)	P_D	188	33.8	W
Derate above 25°C		1.5	0.27	W/°C
Single pulse avalanche energy **(Note 2)**	E_{AS}	144		mJ
Avalanche current **(Note 1)**	I_{AR}	6		A
Repetitive Avalanche energy ， t_{AR} limited by T_{Jmax} **(Note 1)**	E_{AR}	0.7		mJ

Parameter	Symbol	NCE80T420	NCE80T420F	Unit
Drain Source voltage slope, V_{DS} ≤480 V,	dv/dt	50		V/ns
Reverse diode dv/dt， V_{DS} ≤480 V,I_{SD}<I_D	dv/dt	15		V/ns
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55...+150		°C

* limited by maximum junction temperature

Table 2. Thermal Characteristic

Parameter	Symbol	NCE80T420	NCE80T420F	Unit
Thermal Resistance，Junction-to-Case（Maximum）	R_{thJC}	0.66	3.69	°C /W
Thermal Resistance，Junction-to-Ambient （Maximum）	R_{thJA}	62.5	80	°C /W

Table 3. Electrical Characteristics (TA=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	800			V
Zero Gate Voltage Drain Current(Tc=25℃)	I_{DSS}	V_{DS}=800V,V_{GS}=0V		0.05	1	μA
Zero Gate Voltage Drain Current(Tc=125℃)	I_{DSS}	V_{DS}=800V,V_{GS}=0V			100	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	3	3.5	4	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=5.5A		350	420	mΩ
Dynamic Characteristics						
Forward Transconductance	g_{FS}	V_{DS} = 20V, I_D = 5.5A		7		S
Input Capacitance	C_{lss}	V_{DS}=50V,V_{GS}=0V, F=1.0MHz		2600		PF
Output Capacitance	C_{oss}			95		PF
Reverse Transfer Capacitance	C_{rss}			7		PF
Total Gate Charge	Q_g	V_{DS}=640V,I_D=11A, V_{GS}=10V		48		nC
Gate-Source Charge	Q_{gs}			17		nC
Gate-Drain Charge	Q_{gd}			14		nC
Switching times						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=480V,I_D=5.5A, R_G=4Ω,V_{GS}=10V		12		nS
Turn-on Rise Time	t_r			7		nS
Turn-Off Delay Time	$t_{d(off)}$			62		nS
Turn-Off Fall Time	t_f			5		nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I_{SD}	T_C=25°C			11	A
Pulsed Source-drain current(Body Diode)	I_{SDM}				44	A
Forward on voltage	V_{SD}	T_j=25°C,I_{SD}=11A,V_{GS}=0V		0.9	1.3	V
Reverse Recovery Time	t_{rr}	T_j=25°C,I_F=11A,di/dt=100A/μs		290		nS
Reverse Recovery Charge	Q_{rr}			2.2		uC
Peak Reverse Recovery Current	I_{rrm}			15		A

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2. T_j=25℃,V_{DD}=50V,V_G=10V, R_G=25Ω

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Safe operating area for TO-220

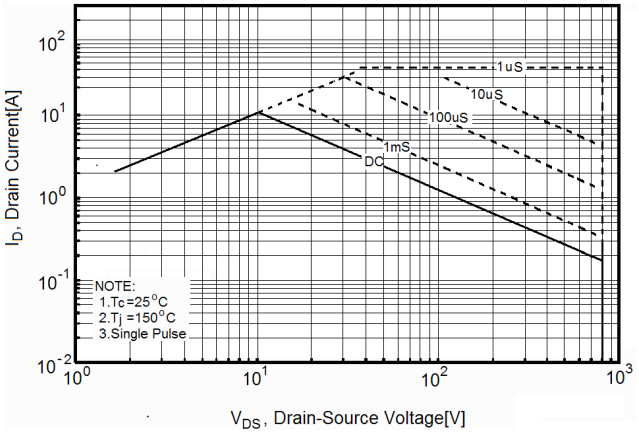


Figure2. Safe operating area for TO-220F

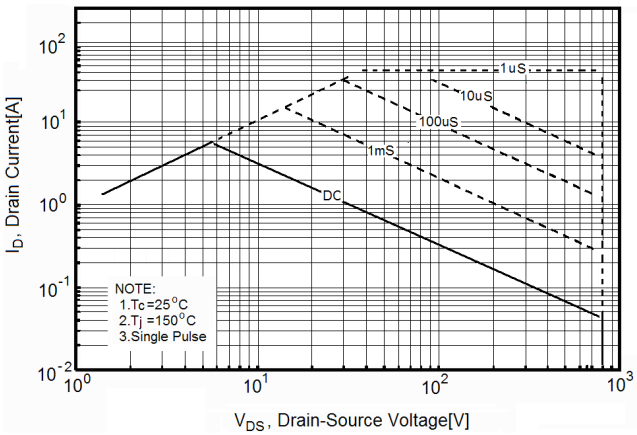


Figure3. Source-Drain Diode Forward Voltage

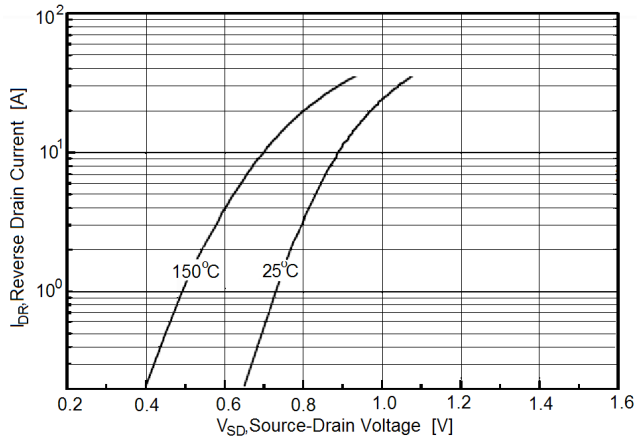


Figure4. Output characteristics

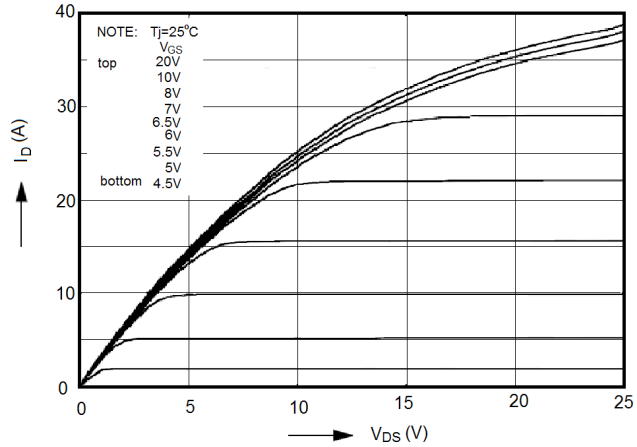


Figure5. Transfer characteristics

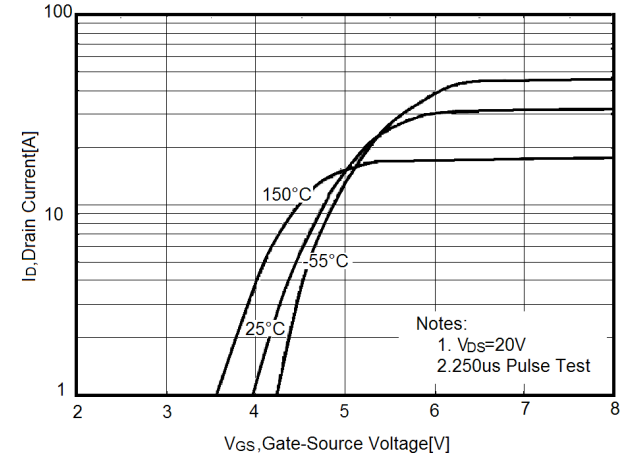


Figure6. Static drain-source on resistance

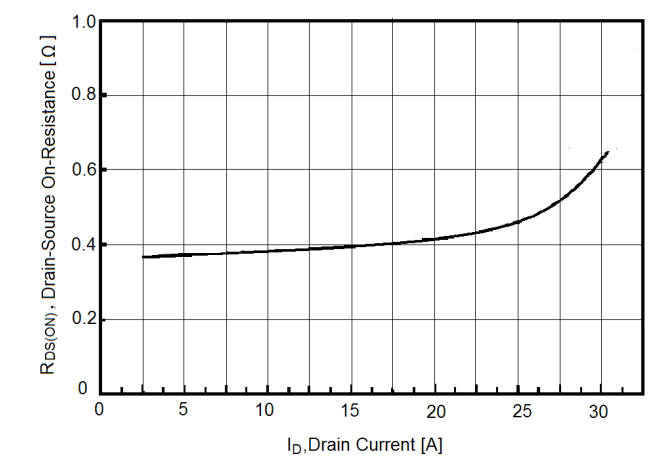


Figure7. $R_{DS(ON)}$ vs Junction Temperature

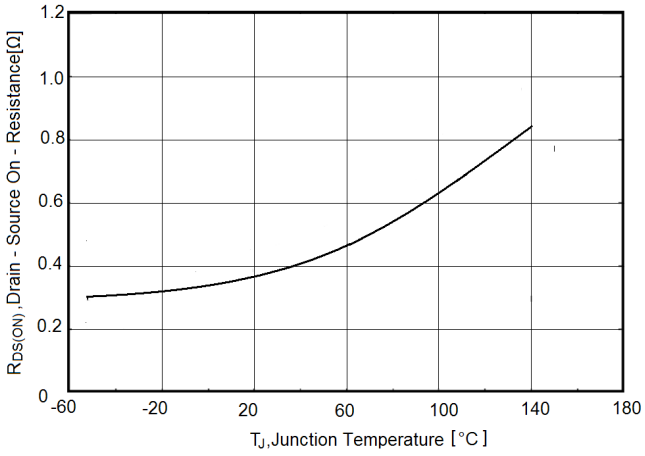


Figure8. BV_{DSS} vs Junction Temperature

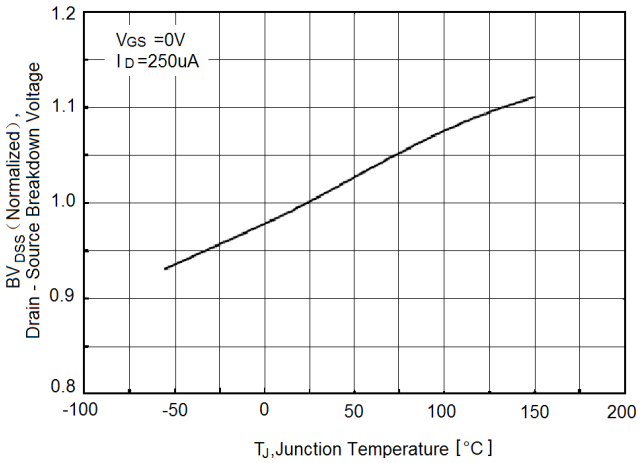


Figure9. Maximum I_D vs Junction Temperature

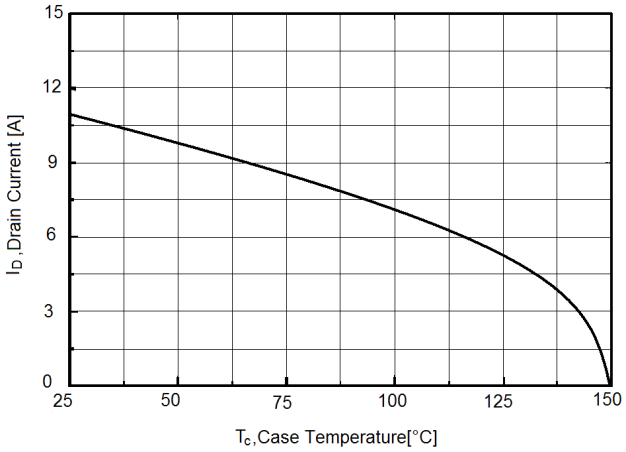


Figure10. Transient Thermal Impedance for TO-220

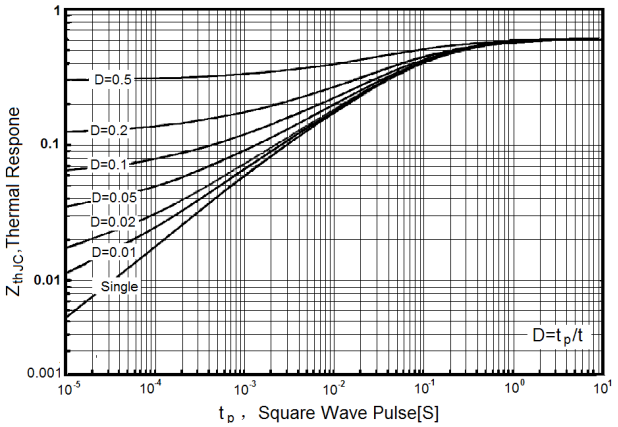
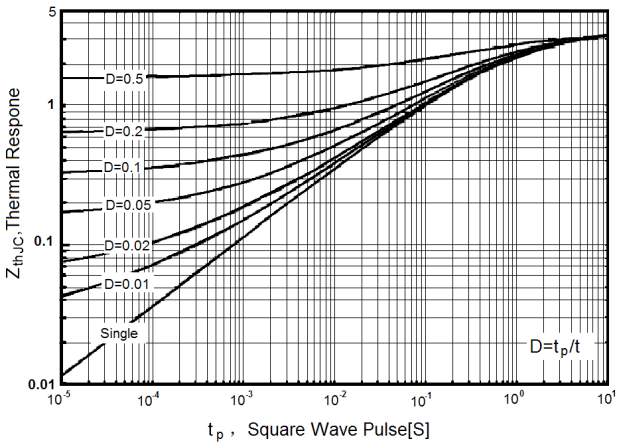
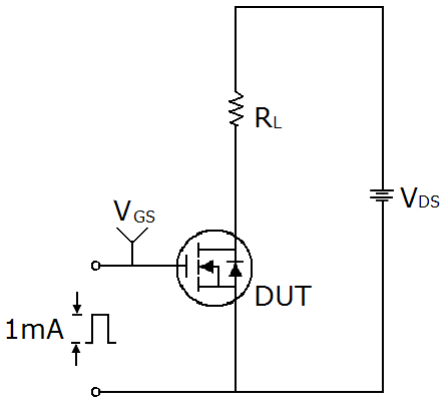


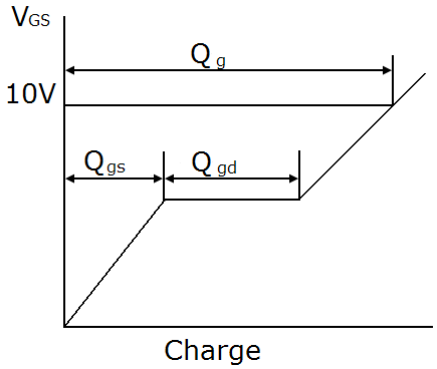
Figure11. Transient Thermal Impedance for TO-220F



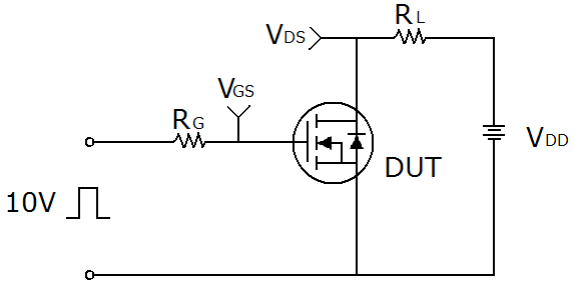
Test circuit

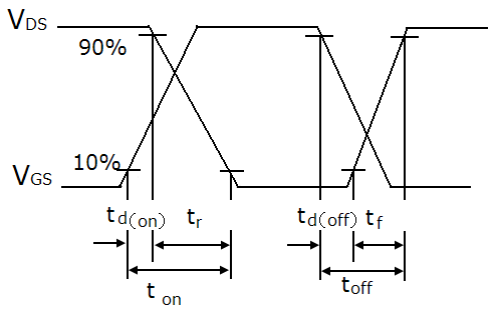
1）Gate charge test circuit & Waveform



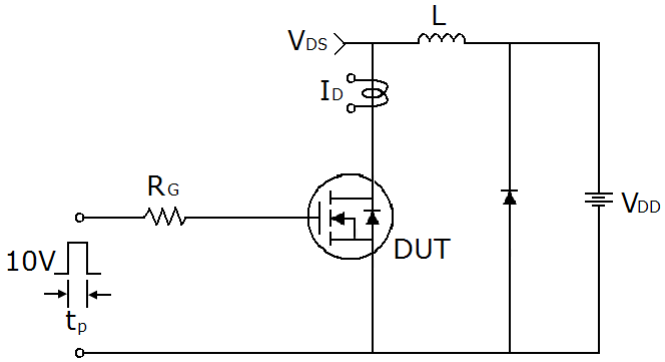


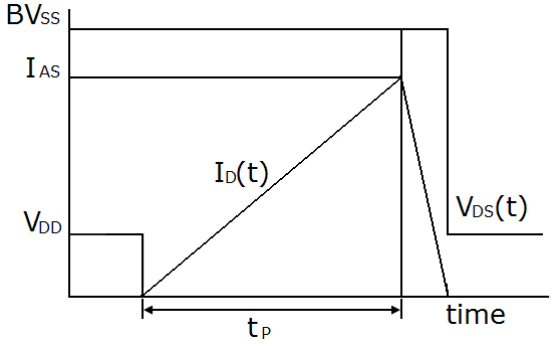
2）Switch Time Test Circuit:



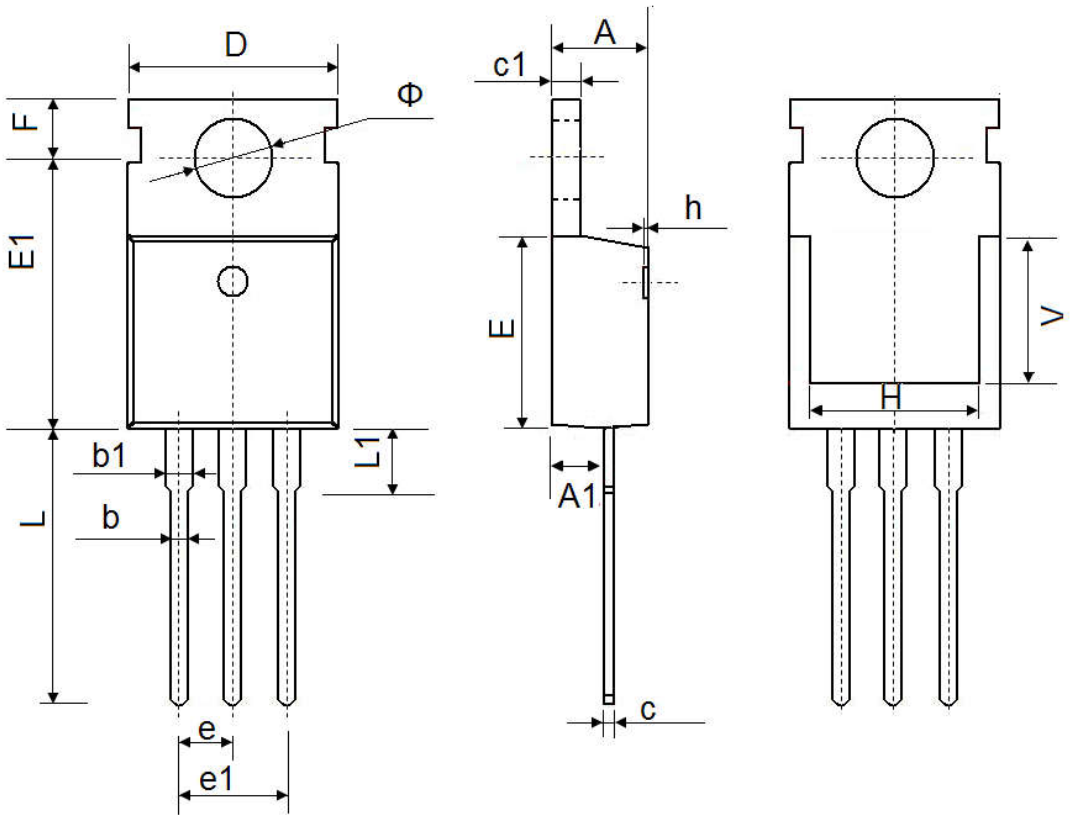


3）Unclamped Inductive Switching Test Circuit & Waveforms



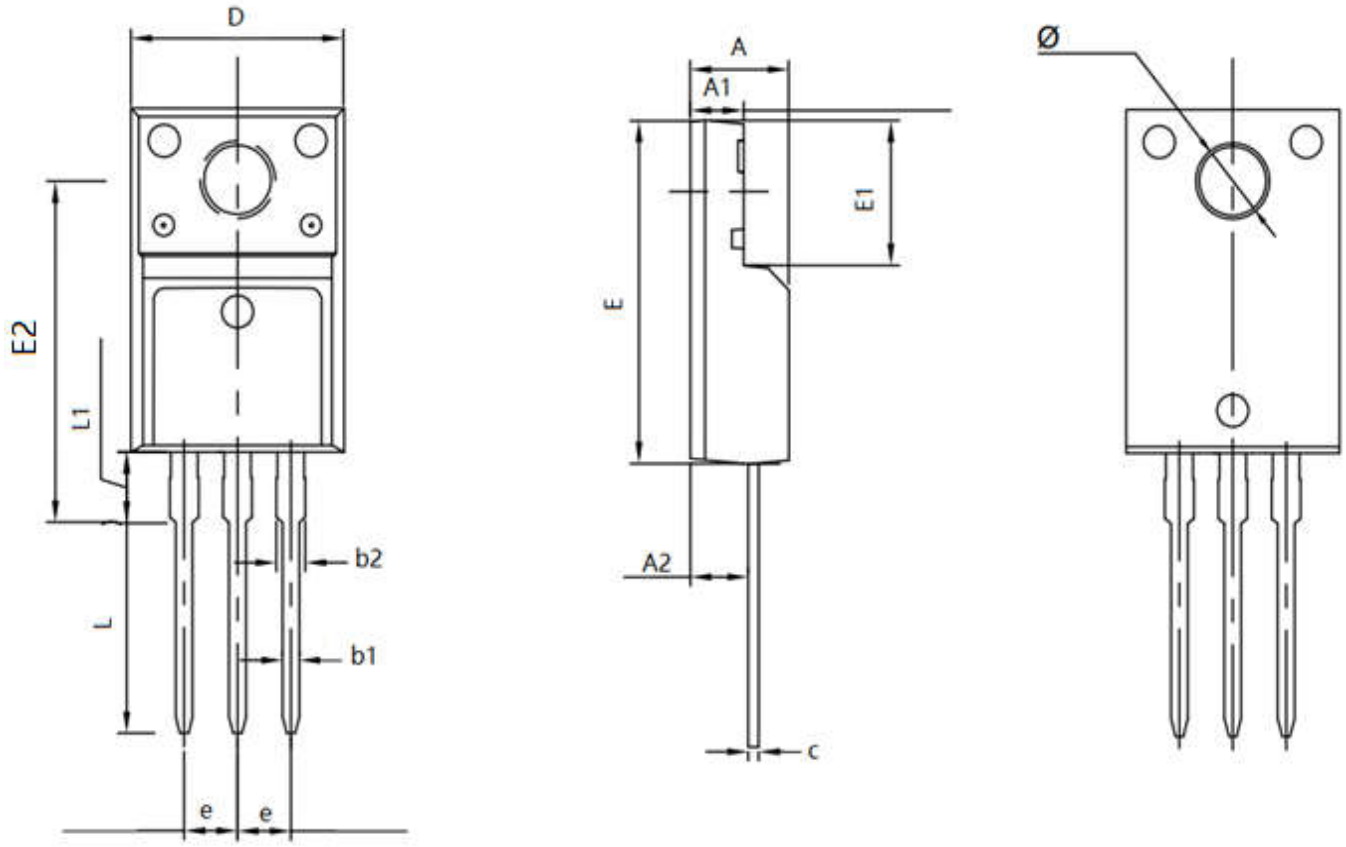


TO-220-3L-C Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
Φ	3.400	3.800	0.134	0.150

TO-220F Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.500	4.900	0.177	0.193
A1	2.340	2.740	0.092	0.108
A2	2.560	2.960	0.101	0.117
b1	0.700	0.900	0.028	0.035
b2	1.180	1.580	0.046	0.062
c	0.400	0.600	0.016	0.024
D	9.960	10.360	0.392	0.408
E	15.670	15.970	0.617	0.629
E1	6.500	6.900	0.256	0.272
E2	15.500	16.100	0.610	0.634
e	2.540 TYP		0.100 TYP	
Φ	3.080	3.280	0.121	0.129
L	12.640	13.240	0.498	0.521
L1	3.030	3.430	0.119	0.135

ATTENTION:

- Any and all NCE products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your NCE representative nearest you before using any NCE products described or contained herein in such applications.
- NCE assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all NCE products described or contained herein.
- Specifications of any and all NCE products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- NCE Power Semiconductor CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all NCE products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of NCE Power Semiconductor CO.,LTD.
- Information (including circuit diagrams and circuit parameters) herein is for example only ; it is not guaranteed for volume production. NCE believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the NCE product that you intend to use.
- This catalog provides information as of Mar. 2010. Specifications and information herein are subject to change without notice.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET ***category:***

Click to view products by NCE Power ***manufacturer:***

Other Similar products are found below :

614233C 648584F MCH3443-TL-E MCH6422-TL-E FDPF9N50NZ FW216A-TL-2W FW231A-TL-E APT5010JVR NTNS3A92PZT5G IRF100S201 JANTX2N5237 2SK2464-TL-E 2SK3818-DL-E FCA20N60_F109 FDZ595PZ STD6600NT4G FSS804-TL-E 2SJ277-DL-E 2SK1691-DL-E 2SK2545(Q,T) D2294UK 405094E 423220D MCH6646-TL-E TPCC8103,L1Q(CM 367-8430-0972-503 VN1206L 424134F 026935X 051075F SBVS138LT1G 614234A 715780A NTNS3166NZT5G 751625C 873612G IRF7380TRHR IPS70R2K0CEAKMA1 RJK60S3DPP-E0#T2 RJK60S5DPK-M0#T0 APT5010JVFR APT12031JFLL APT12040JVR DMN3404LQ-7 NTE6400 JANTX2N6796U JANTX2N6784U JANTXV2N5416U4 SQM110N05-06L-GE3 SIHF35N60E-GE3